

AMENDMENTS TO THE CLAIMS

1-10 (Canceled)

11. (Currently Amended) An array substrate for a transfective liquid crystal display device, the substrate comprising;

a gate line and a data line defining a pixel region by crossing each other;

a switching element at a crossing portion of the gate line and the data line;

a first passivation layer covering the switching element and the data line, the first passivation layer being formed of an inorganic insulating material;

a reflective electrode on and directly contacting the first passivation layer, the reflective electrode being connected to the switching element and including a transmission hole;

a second passivation layer on the reflective electrode, the second passivation layer being formed of organic insulating material and patterned to expose a part of the switching element; and

a transparent pixel electrode on and directly contacting the second passivation layer, the pixel electrode being formed in the pixel region and contacting the exposed part of the switching element.

12. (Original) The device according to claim 11, wherein the reflective electrode is formed of a conductive metal material including aluminum (Al) or aluminum alloys.

13. (Original) The device according to claim 11, wherein the switching element is a thin film transistor including a gate electrode, a source electrode, a drain electrode and an active layer.

14. (Original) The device according to claim 11, wherein the first passivation layer is formed of silicon nitride (SiN_x).

15. (Original) The device according to claim 11, wherein the second passivation layer is formed of an organic insulating material including benzocyclobutene (BCB) or an acrylic resin.

16. (Currently Amended) A manufacturing method of an array substrate for a transflective liquid crystal display device, the method comprising the steps of:

forming a gate line and a data line defining a pixel region by crossing each other;

forming a switching element at a crossing portion of the gate line and the data line;

forming a first passivation layer covering the switching element and the data line, the first passivation layer being formed of an inorganic insulating material;

forming a reflective electrode on and directly contacting the first passivation layer, the reflective electrode being connected to the switching element and including a transmission hole;

forming a second passivation layer on the reflective electrode, the second passivation layer being formed of an organic insulating material and patterned to expose a part of the switching element; and

forming a transparent pixel electrode on the second passivation layer, the pixel electrode being formed in the pixel region and contacting the exposed part of the switching element.

17. (Original) The method according to claim 16, wherein the reflective electrode is formed of a conductive metal material including aluminum (Al) or an aluminum alloy.

18. (Original) The method according to claim 16, wherein

the switching element is a thin film transistor including a gate electrode, a source electrode, a drain electrode and an active layer.

19. (Original) The method according to claim 16, wherein the first passivation layer is formed of silicon nitride (SiN_x).

20. (Original) The method according to claim 16, wherein the second passivation layer is formed of an organic insulating material including benzocyclobutene (BCB) or acrylic resin.

21-43. (Canceled)